CMH50N60/CMA50N60

600V, 150mΩ typ., 50A N-Channel MOSFET

General Description

These Power MOSFETs are produced using Cmos's proprietary, planar stripe, DMOS technology. These devices are well suited for high efficiency switch mode power supply.

Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
600V	180mΩ	50A

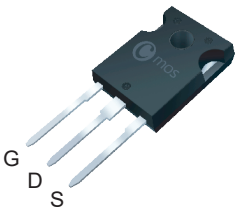
Applications

- DC-DC converters
- Uninterruptible Power Supply

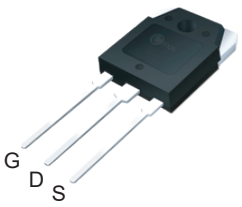
Features

- 100% avalanche tested
- Improve dv/dt capability
- RoHS compliant

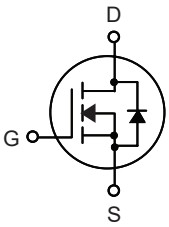
TO-247/TO-3P Pin Configuration



TO-247
CMH50N60



TO-3P
CMA50N60



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D@T_C=25℃	Continuous Drain Current	50	A
I_D@T_C=100℃	Continuous Drain Current	35	A
I_{DM}	Pulsed Drain Current	200	A
EAS	Single Pulse Avalanche Energy (Note 1)	5120	mJ
P_D@T_C=25℃	Total Power Dissipation	600	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.21	℃/W

600V, 150mΩ typ., 50A N-Channel MOSFET

Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	600	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	150	180	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V , V_{GS}=0V	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V , V_{DS}=0V	---	---	±250	nA
gfs	Forward Transconductance	V_{DS}=20V , I_D =20A	---	45	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.8	---	Ω
Q_g	Total Gate Charge	V_{DD} =300V , I_D=25A V_{GS}=10V	---	---	---	nC
Q_{gs}	Gate-Source Charge		---	---	---	
Q_{gd}	Gate-Drain Charge		---	---	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=300V , I_D =25A R_G =10Ω , V_{GS}=10V	---	---	---	ns
T_r	Rise Time		---	---	---	
$T_{d(off)}$	Turn-Off Delay Time		---	---	---	
T_f	Fall Time		---	---	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	8950	---	pF
C_{oss}	Output Capacitance		---	270	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	50	A
I_{SM}	Pulsed Source Current		---	---	200	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=40A ,T_J=25℃	---	0.88	1.5	V
t_{rr}	Reverse Recovery Time	di/dt = 100A/μs V_{GS}=0V , I_{SD}=40A	---	---	---	ns
Q_{rr}	Reverse Recovery Charge		---	---	---	μC

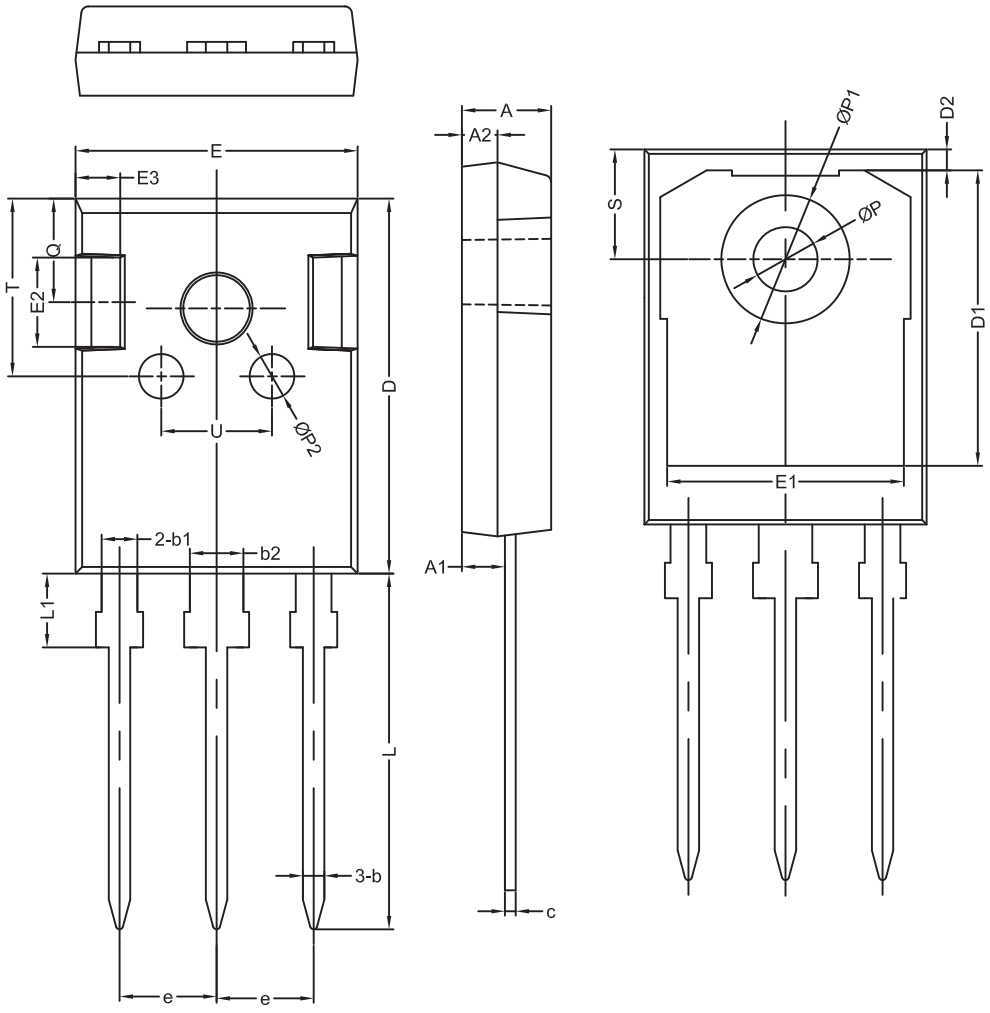
Note :

1. The EAS data shows Max. rating .The test condition is V_{DS}=120V , V_{GS}=10V , L=10mH , I_{AS}=32A.

This product has been designed and qualified for the counsumer market.
Cmos assumes no liability for customers' product design or applications.
Cmos reserver the right to improve product design ,functions and reliability wihtout notice.Please refer to the latest version of specification.

Package Dimension

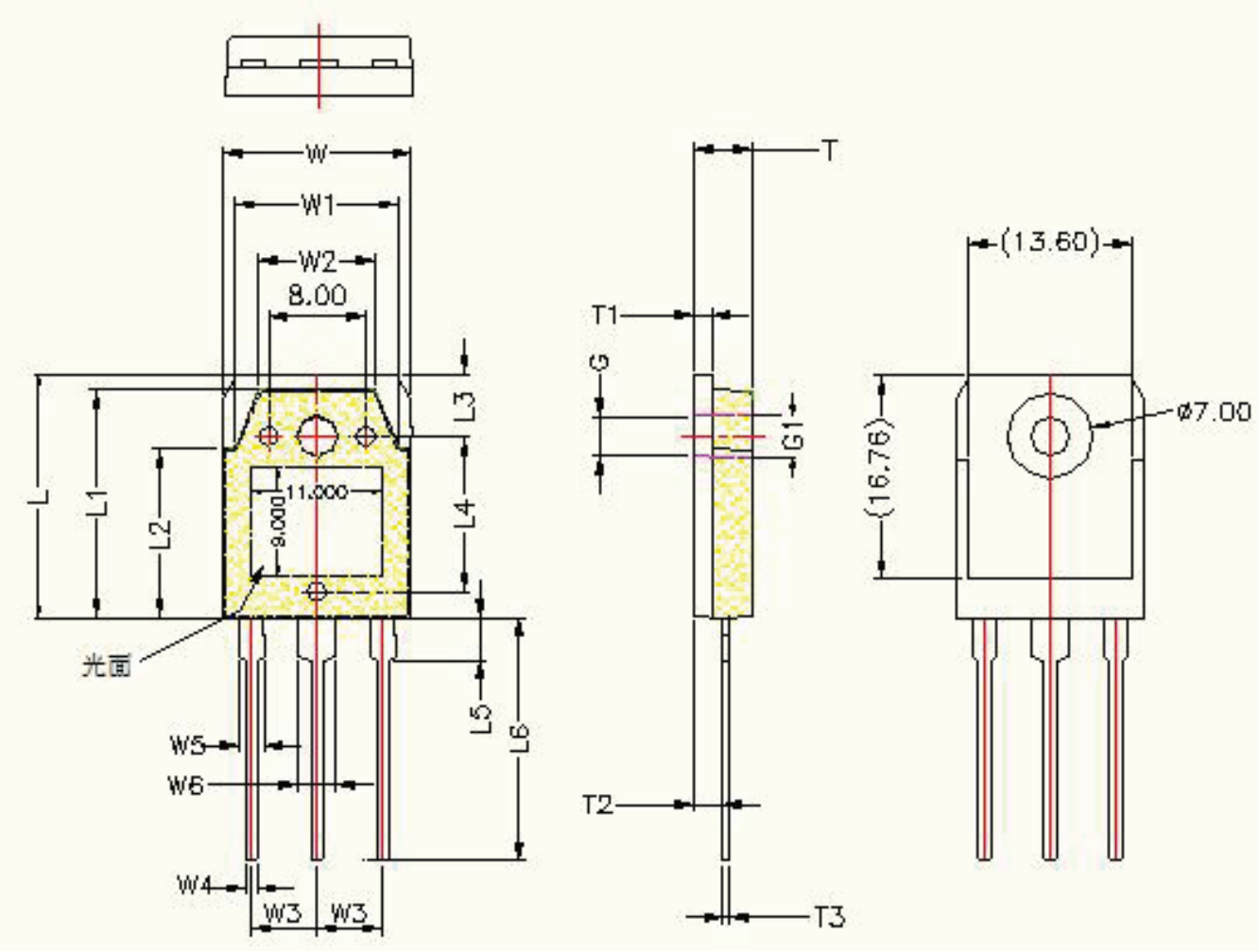
TO-247 Unit :mm



符号	机械尺寸/mm			符号	机械尺寸/mm		
	最小值	典型值	最大值		最小值	典型值	最大值
A	4.80	5.00	5.20	E2		5.00	
A1	2.21	2.41	2.61	E3		2.50	
A2	1.90	2.00	2.10	e		5.44	
b	1.10	1.20	1.35	L	19.42	19.92	20.42
b1		2.00		L1		4.13	
b2		3.00		P	3.50	3.60	3.70
c	0.55	0.60	0.75	P1		7.19	
D	20.80	21.00	21.20	P2		2.50	
D1		16.55		Q		5.80	
D2		1.20		S	6.05	6.15	6.25
E	15.60	15.80	16.0	T		10.00	
E1		13.30		U		6.20	

Package Dimension

TO-3P Unit :mm



Symbol	Dimensions	Symbol	Dimensions	Symbol	Dimensions
W	15.60±0.3	L	19.90±0.3	T	4.80±0.3
W1	13.60±0.3	L1	18.70±0.3	T1	1.50±0.3
W2	9.60±0.3	L2	13.90±0.3	T2	2.40±0.3
W3	5.45(TYP)	L3	5.00±0.3	T3	0.60±0.3
W4	1.00±0.3	L4	12.76±0.3	G	Ø3.25±0.3
W5	2.10±0.2	L5	3.50±0.3	G1	Ø3.58±0.3
W6	3.10±0.2	L6	20.00±0.3		